

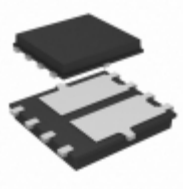
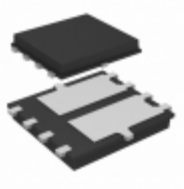


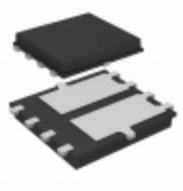
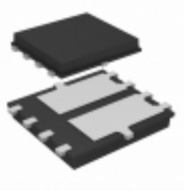

	<h2>SI7923DN-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SI7923DN-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET 2P-CH 30V 4.3A 1212-8</p> <p>Datenblätter:  SI7923DN-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 6527 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7923DN-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET 2P-CH 30V 4.3A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	6527 pcs Stock
Hersteller Standard Vorlaufzeit	33 Weeks
detaillierte Beschreibung	Mosfet Array 2 P-Channel (Dual) 30V 4.3A 1.3W
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.3W
Verpackung / Gehäuse	PowerPAK® 1212-8 Dual
Supplier Device-Gehäuse	PowerPAK® 1212-8 Dual
Typ FET	2 P-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.3A
Rds On (Max) @ Id, Vgs	47 mOhm @ 6.4A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	21nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)
Basisteilenummer	SI7923
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7923DN-T1-GE3TR

SI7923DN-T1-GE3 ist neu im Original, Suche SI7923DN-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7923DN-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7923DN-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7925DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2P-CH 12V 4.8A 1212-8</p>	 <p>SI7925DN-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2P-CH 12V 4.8A 1212-8</p>	 <p>SI7923DN-T1-GE3 Vishay / Siliconix MOSFET 2P-CH 30V 4.3A 1212-8</p>	 <p>SI7923DN-T1-e3ct-nd VISHAY SI7923DN-T1-e3ct-nd VISHAY</p>
 <p>SI7922DN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 100V 1.8A 1212-8</p>	 <p>SI7923DN-T1-E3 Vishay / Siliconix MOSFET 2P-CH 30V 4.3A 1212-8</p>	 <p>SI7925DN-T1-E3 Vishay / Siliconix MOSFET 2P-CH 12V 4.8A 1212-8</p>	 <p>SI7925DN SI SI7925DN SI</p>

heiße Teile

Mehr

SI7904DN-T1-E3	SI7904DN-T1-E3	SI7904DN-T1-GE3	SI7904DN-T1-GE3	SI7905DN-T1-GE3
SI7905DN-T1-GE3	SI7909DN-T1-E3	SI7909DN-T1-E3	SI7909DN-T1-GE3	SI7909DN-T1-GE3
SI7911DN	SI7911DN-T1-E3	SI7911DN-T1-E3	SI7911DN-T1-GE3	SI7911DN-T1-GE3
SI7913DN-T1-E3	SI7913DN-T1-E3	SI7913DN-T1-GE3	SI7913DN-T1-GE3	SI7922DN-T1-E3
SI7922DN-T1-E3	SI7922DN-T1-GE3	SI7922DN-T1-GE3	SI7923DN-T1-E3	SI7923DN-T1-E3
SI7923DN-T1-GE3	SI7938DP-T1-GE3	SI7938DP-T1-GE3	SI7940DP	SI7940DP-T1-E3
SI7940DP-T1-E3	SI7941DP-T1-E3	SI7941DP-T1-GE3	SI7942DP	SI7942DP-T1-E3
SI7942DP-T1-E3	SI7942DP-T1-GE3	SI7942DP-T1-GE3	SI7945DP-T1-E3	SI7945DP-T1-E3
SI7946DP	SI7946DP-T1-E3	SI7946DP-T1-E3	SI7948DP	SI7948DP-T1-E3
SI7949DP-T1-GE3	SI7949DP-T1-GE3	SI7956DP-T1-GE3	SI7956DP-T1-GE3	SI7958DP

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